IN THE CLAIMS

1 (Previously Amended). A reflector comprising:

a reflective layer; and

an absorbing layer that preferentially absorbs blue light, said absorbing layer being located over said reflective layer, said absorbing layer including about 700 to about 750 Angstroms of silicon dioxide and about 700 to about 750 Angstroms of silicon nitride.

2 (Original). The reflector of claim 1 wherein said reflector is a micromirror.

3 (Original). The reflector of claim 1 wherein said reflective layer is formed of silver, said silver being formed over a polished semiconductor material.

4 (Original). The reflector of claim 3 wherein said silver layer is covered by an insulator.

5 (Original). The reflector of claim 3 wherein the absorbing layer includes silicon nitride.

6 (Original). The reflector of claim 4 wherein said absorbing layer includes silicon dioxide.

Claim 7 (Canceled).

8 (Previously Amended). A method comprising:

forming a reflective layer; and

forming an absorbing layer, including oxide and nitride layers of a thickness of about 700 to about 750 Angstroms over said reflective layer, that absorbs a particular wavelength of light.

9 (Original). The method of claim 8 including forming a reflective layer by depositing silver on a semiconductor layer.

10 (Original). The method of claim 8 including forming an absorbing layer including a layer of two different insulator materials.

11 (Original). The method of claim 9 including forming said silver layer at a temperature of 50°C or less.

12 (Original). The method of claim 10 including forming said absorbing layer at a temperature of less than 250°C.

13 (Original). The method of claim 12 including forming said absorbing layer using chemical vapor deposition.

Claims 14-15 (Canceled).

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16 (Currently Amended). A reflector comprising:

a silicon substrate; ~~and~~

a silver layer formed directly on said silicon substrate; and

an absorbing layer over said silver layer, said absorbing layer including about 700 to 750 Angstroms of silicon dioxide and from 700 to about 750 Angstroms of silicon nitride.

17 (Original). The reflector of claim 16 wherein said reflector is a micromirror.

Claim 18 (Canceled).

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19 (Currently Amended). The reflector of claim ~~18~~ 16 wherein said absorbing layer preferentially absorbs blue light.

Claims 20-22 (Canceled).

23. The reflector of claim 16 wherein said silver layer is formed at a temperature below 50°C.

24 (Previously Amended). The reflector of claim 18 wherein said absorbing layer is formed at a temperature below 250°C.

25 (Original). A method comprising:

depositing silver on a silicon substrate at a temperature less than 50°C; and

forming an absorbing layer over said silver.

26 (Original). The method of claim 25 including forming an absorbing layer including a layer of two different insulator materials.

27 (Original). The method of claim 26 including forming said absorbing layer at a temperature of less than 250°C.

28 (Original). The method of claim 26 including forming said absorbing layer of a layer of oxide and a layer of nitride.

29 (Original). The method of claim 28 including forming said oxide and nitride layers of a thickness of about 700 to about 750 Angstroms.

30 (Previously Amended). The method of claim 29 including depositing said oxide and nitride layers using chemical vapor deposition.